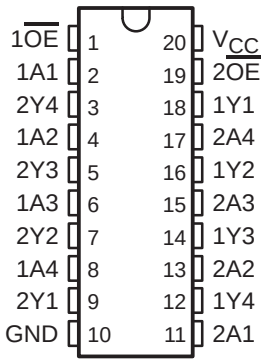
SN54ABT2240A, SN74ABT2240A
OCTAL BUFFERS AND LINE/MOS DRIVERS WITH 3-STATE OUTPUTS

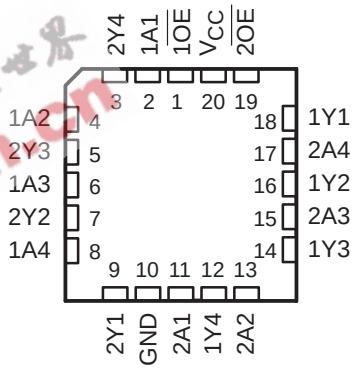
SCBS232E – JANUARY 1991 – REVISED OCTOBER 1998

- **Output Ports Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **State-of-the-Art *EPIC*-II*B*™ BiCMOS Design Significantly Reduces Power Dissipation**
- **Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Plastic (N) and Ceramic (J) DIPs, and Ceramic Flat (W) Package**

SN54ABT2240A . . . J OR W PACKAGE
SN74ABT2240A . . . DB, DW, N, OR PW PACKAGE
(TOP VIEW)



SN54ABT2240A . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers and line drivers are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. Together with the ’ABT2241 and ’ABT2244A, these devices provide combinations of inverting and noninverting outputs, symmetrical active-low output-enable ($\overline{OE}$) inputs, and complementary OE and $\overline{OE}$ inputs. These devices feature high fan-out and improved fan-in.

These devices are organized as two 4-bit line drivers with separate $\overline{OE}$ inputs. When $\overline{OE}$ is low, the devices pass inverted data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include equivalent 25-Ω series resistors to reduce overshoot and undershoot.

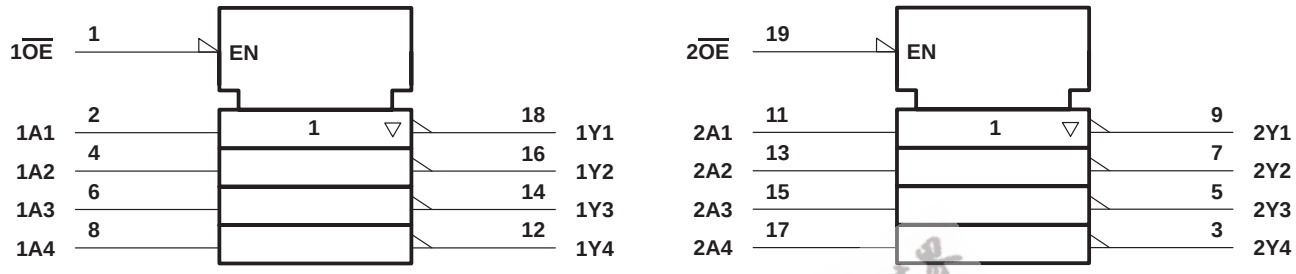
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54ABT2240A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT2240A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

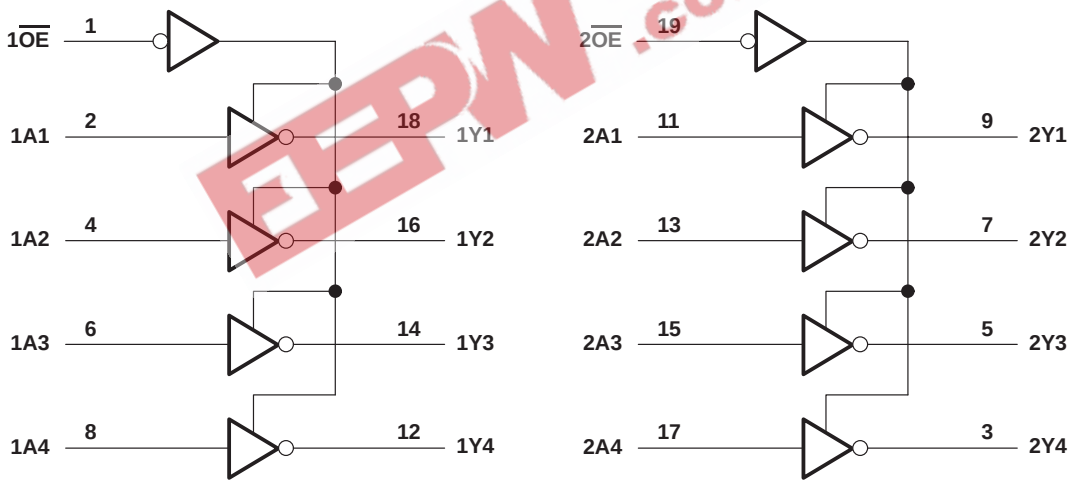
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†

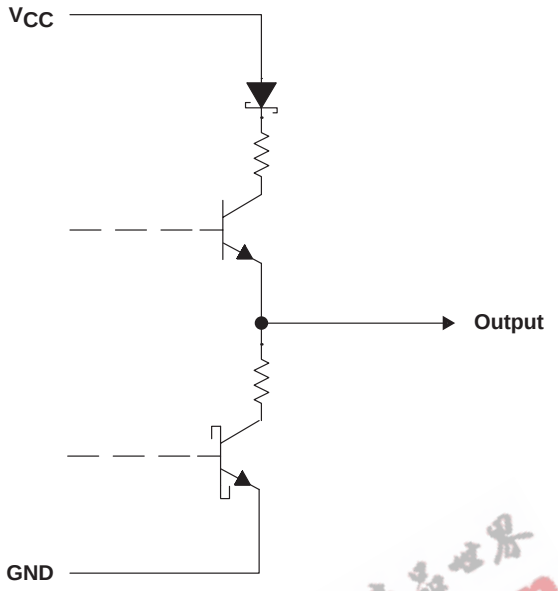


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



schematic of Y outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O . . . . . –0.5 V to 5.5 V
Current into any output in the low state, I_O . . . . . 30 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –18 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package . . . . . 115°C/W
DW package . . . . . 97°C/W
N package . . . . . 67°C/W
PW package . . . . . 128°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions (see Note 3)

			SN54ABT2240A		SN74ABT2240A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		5		5	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A = 25°C			SN54ABT2240A		SN74ABT2240A		UNIT
				MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V_{IK}		V_{CC} = 4.5 V,	I_I = –18 mA			–1.2		–1.2		–1.2	V
V_{OH}		V_{CC} = 4.5 V,	I_{OH} = –3 mA	2.5			2.5		2.5		V
		V_{CC} = 5 V,	I_{OH} = –3 mA	3			3		3		
		V_{CC} = 4.5 V	I_{OH} = –24 mA	2			2				
			I_{OH} = –32 mA	2*					2		
V_{OL}		V_{CC} = 4.5 V,	I_{OL} = 12 mA			0.8		0.8		0.8	V
V_{hys}					100						mV
I_I		V_{CC} = 5.5 V,	V_I = V_{CC} or GND			±1		±1		±1	µA
I_{OZH}		V_{CC} = 5.5 V,	V_O = 2.7 V			10*		10		10	µA
I_{OZL}		V_{CC} = 5.5 V,	V_O = 0.5 V			–10*		–10		–10	µA
I_{off}		V_{CC} = 0,	V_I or $V_O \le$ 4.5 V			±100				±100	µA
I_{CEX}		V_{CC} = 5.5 V, V_O = 5.5 V	Outputs high			50		50		50	µA
I_O‡		V_{CC} = 5.5 V,	V_O = 2.5 V	–50	–100	–180	–50	–180	–50	–180	mA
I_{CC}		V_{CC} = 5.5 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		1	250		250		250	µA
			Outputs low		24	30		30		30	mA
			Outputs disabled		0.5	250		250		250	µA
ΔI_{CC}§	Data inputs	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND	Outputs enabled			1.5		1.5		1.5	mA
			Outputs disabled			0.05		0.05		0.05	
	Control inputs	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND				1.5		1.5		1.5	
C_i		V_I = 2.5 V or 0.5 V			4						pF
C_o		V_O = 2.5 V or 0.5 V			7						pF

* On products compliant to MIL-PRF-38535, this parameter does not apply.
† All typical values are at V_{CC} = 5 V.
‡ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

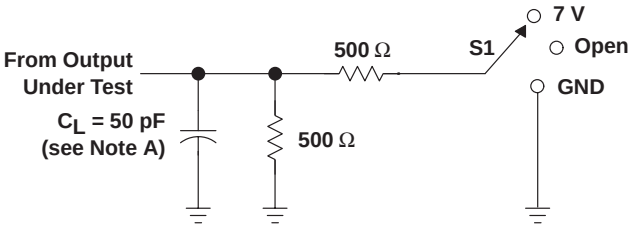
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ABT2240A					UNIT
			V_{CC} = 5 V, T_A = 25°C			MIN	MAX	
			MIN	TYP	MAX			
t_{PLH}	A	Y	1	3	4	1	5	ns
t_{PHL}			2.1	4.8	5.8	2.1	6.3	
t_{PZH}	$\overline{OE}$	Y	1.5	3.7	4.7	1.5	6.1	ns
t_{PZL}			1.7	6.5	7.6	1.7	8.8	
t_{PHZ}	$\overline{OE}$	Y	1.8	3.8	6.4	1.5	6.8	ns
t_{PLZ}			1	4.7	5.8	1	6.9	

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

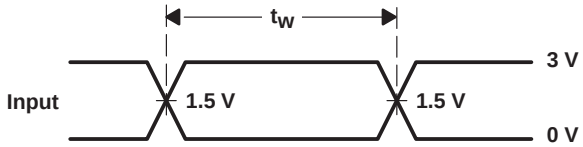
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74ABT2240A					UNIT
			V_{CC} = 5 V, T_A = 25°C			MIN	MAX	
			MIN	TYP	MAX			
t_{PLH}	A	Y	1	3	4.1	1	4.8	ns
t_{PHL}			2.1	4.1	5.1	2.1	5.4	
t_{PZH}	$\overline{OE}$	Y	1.1	3.1	4.7	1.1	5.2	ns
t_{PZL}			1.7	4.5	6.4	1.7	6.8	
t_{PHZ}	$\overline{OE}$	Y	1.8	3.4	5.7	1.8	6.4	ns
t_{PLZ}			1.9	3.6	6	1.9	6.2	

PARAMETER MEASUREMENT INFORMATION

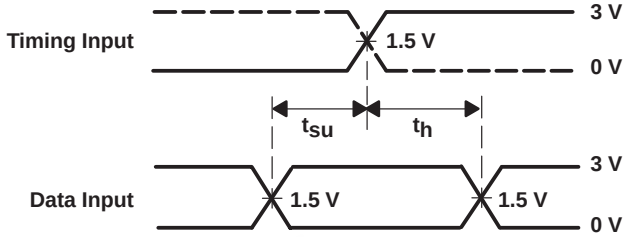


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open

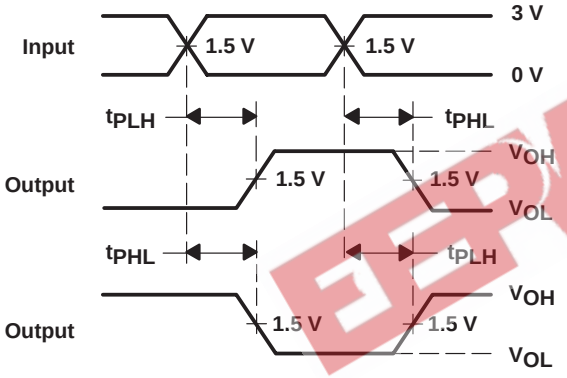
LOAD CIRCUIT



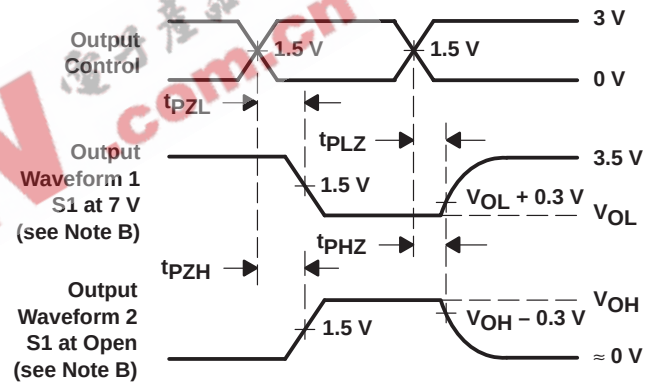
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.